



2814

Docket No.: M4065.0475/P475-A  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

John Moore

09/938,672

Application No.: Not Yet Assigned

Filed: February 13, 2003

For: APPARATUS AND METHOD OF  
FABRICATING DUAL PCRAM CELLS  
SHARING A COMMON ELECTRODE  
PCRAM MEMORY DEVICE

#13 Suppl IDS

Group Art Unit: 2151

Examiner: Not Yet Assigned

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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents  
Washington, DC 20231

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO/SB/08. It is respectfully requested that the subject matter of the documents be expressly considered during the prosecution of this application and that the documents be made of record therein and appear among the "References Cited" on any patent to issue from this application. A copy of each document is attached.

This Information Disclosure Statement is filed before the mailing date of a first Office Action on the merits as far as is known to the undersigned.

A brief explanation of relevance of the non-patent documents listed on form PTO/SB/08 is provided and attached hereto as Appendix A. The brief explanation provided for each document is not tantamount to an admission that a document is "material" or that it qualifies as prior art. The Examiner is respectfully requested to utilize

Appendix A only as a tool by which to better categorize the documents for substantive use in examining the claims of the application.

Documents discussed in Appendix A marked with an asterisk (\*) are indicated to be potentially more relevant than others. Such marking is provided only to assist the Examiner; however, the Examiner is requested to thoroughly review all documents cited herein.

In accordance with 37 C.F.R. § 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 C.F.R. § 1.56(a) exists. It is submitted that the Information Disclosure Statement is in compliance with 37 C.F.R. § 1.98 and the Examiner is respectfully requested to consider and cite the listed documents.

The Commissioner is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0475/P475. A duplicate copy of this paper is enclosed.

Dated: March 17, 2003

Respectfully submitted,

By

Thomas J. D'Amico

Registration No.: 28,371

Ryan H. Flax

Registration No.: 48,141

DICKSTEIN SHAPIRO MORIN &

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Attorneys for Applicant

## APPENDIX A

Japanese patent application publication No. 56126916A by Akira: this published application generally relates to, inter alia, diffusing selenium with high accuracy into a chalcogenide with silver by use of photoresist and thermal treatment.

\*Axon Technologies Corp., *Technology Description: Programmable Metallization Cell*: this believed publication generally relates to, inter alia, use of chalcogenides doped with metal such as silver or copper to create solid state switch with lower voltage requirement.

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In re Patent Application of:  
John Moore

Application No.: 09/938,672

Group Art Unit: 2151

Filed: August 27, 2001

Examiner: T. Washington

For: METHOD OF FABRICATING DUAL  
PCRAM CELLS SHARING A COMMON  
ELECTRODE

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**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
Washington, DC 20231

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01 FC:1B06 100.00 0P

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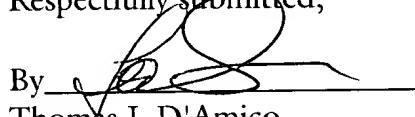
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